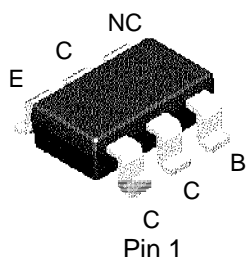


FMBS549



Package: SuperSOT-6 single
Mark : .S1

PNP Low Saturation Transistor

This device is designed with high current gain and low saturation voltage with collector currents up to 2A continuous. Sourced from process PB.

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	35	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous - Peak Pulse Current	1 2	A A
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150°C .
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Characteristics	Max	Units
P_D	Total Device Dissipation*	700	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, total	180	$^\circ\text{C/W}$

*Device mounted on a 1 in2 pad of 2 oz copper.

PNP Low Saturation transistor
(continued)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
BV_{CEO}	Collector to Emitter Voltage	$I_c = 10\text{ mA}$	30		V
BV_{CBO}	Collector to Base Voltage	$I_c = 100\text{ }\mu\text{A}$	35		V
BV_{EBO}	Emitter to Base Voltage	$I_e = 100\text{ }\mu\text{A}$	5		V
I_{CBO}	Collector Cutoff Current	$V_{cb} = 30\text{ V}$ $V_{cb} = 30\text{ V}, T_a = 100^\circ\text{C}$		100 10	nA μA
I_{EBO}	Emitter Cutoff Current	$V_{eb} = 4\text{ V}$		100	nA
ON CHARACTERISTICS					
h_{FE}	DC Current Gain	$V_{ce} = 2\text{ V}, I_c = 50\text{ mA}$ $V_{ce} = 2\text{ V}, I_c = 500\text{ mA}$ $V_{ce} = 2\text{ V}, I_c = 1\text{ A}$ $V_{ce} = 2\text{ V}, I_c = 2\text{ A}$ $V_{ce} = 0.8\text{ V}, I_c = 500\text{ mA}$	70 100 80 40 100	300	-
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_c = 250\text{ mA}, I_b = 25\text{ mA}$ $I_c = 500\text{ mA}, I_b = 50\text{ mA}$ $I_c = 1\text{ A}, I_b = 100\text{ mA}$ $I_c = 2\text{ A}, I_b = 200\text{ mA}$		200 350 500 750	mV mV mV mV
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_c = 1\text{ A}, I_b = 100\text{ mA}$		1.25	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_c = 1\text{ A}, V_{ce} = 2\text{ V}$		1	V
SMALL SIGNAL CHARACTERISTICS					
C_{obo}	Output Capacitance	$V_{cb} = 10\text{ V}, f = 1\text{ MHz}$		25	pF
f_T	Current Gain - Bandwidth Product	$V_{ce} = 5\text{ V}, I_c = 100\text{ mA}, f = 100\text{ MHz}$	100		MHz

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FACT Quiet Series™	QS™	
FAST®	Quiet Series™	
FASTr™	SuperSOT™-3	
GTO™	SuperSOT™-6	
HiSeC™	SuperSOT™-8	

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PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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